

RJQ6008DPM

600V - 10A - IGBT and Diode
High Speed Power Switching

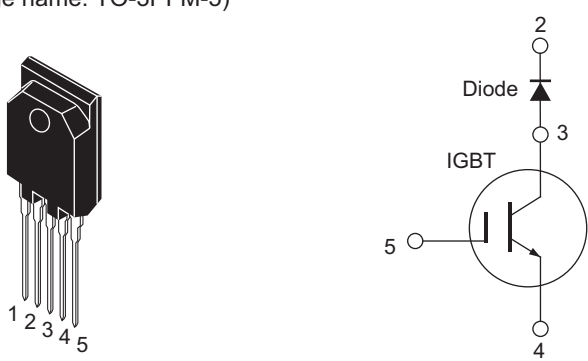
R07DS0847EJ0100
Rev.1.00
Jul 17, 2012

Features

- Low collector to emitter saturation voltage
 $V_{CE(sat)} = 2.65 \text{ V typ. (} I_C = 25 \text{ A, } V_{GE} = 15 \text{ V, } T_a = 25^\circ\text{C)}$
- Built in fast recovery diode in one package
- Trench gate and thin wafer technology
- High speed switching

Outline

RENESAS Package code: PRSS0005ZB-A
(Package name: TO-3PFM-5)



1. NC
2. Cathode
3. Anode, Collector
4. Emitter
5. Gate

Absolute Maximum Ratings

IGBT

($T_c = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	600	V
Gate to emitter voltage	V_{GES}	± 30	V
Collector current	I_C ^{Note1}	20	A
	I_C ^{Note1}	10	A
Collector peak current	$I_{C(peak)}$ ^{Note3}	100	A
Collector dissipation	P_C ^{Note2}	48	W
Junction to case thermal impedance	θ_{j-c}	2.3	$^\circ\text{C/W}$
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes: 1. Limited by T_j max.
2. Value at $T_c = 25^\circ\text{C}$
3. Pulse width limited by maximum safe operating area.

Diode

(Tc = 25°C)

Item	Symbol	Ratings	Unit
Maximum reverse voltage	V_{RM}	600	V
Average rectified forward current	I_o	20	A
Peak surge forward current	PW = 10 ms	I_{FSM} ^{Note4}	A
	PW = 1 ms	I_{FSM} ^{Note5}	A
Junction to case thermal impedance	θ_{j-cd}	3.0	°C/W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 4. 50Hz sine half wave, Non-repetitive 1 cycle value, Tj = 25°C.

5. PW = 1ms sine half wave, Non-repetitive peak value, Tj = 25°C.

Electrical Characteristics

IGBT

(Tj = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage collector current	I_{CES}	—	—	10	μA	$V_{CE} = 600\text{ V}, V_{GE} = 0$
Gate to emitter leak current	I_{GES}	—	—	±1	μA	$V_{GE} = \pm 30\text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	3.0	—	5.5	V	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	2.65	3.5	V	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$ ^{Note6}
	$V_{CE(sat)}$	—	3.2	—	V	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ ^{Note6}
Input capacitance	C_{ies}	—	1800	—	pF	$V_{CE} = 25\text{ V}$
Output capacitance	C_{oes}	—	200	—	pF	$V_{GE} = 0$
Reveres transfer capacitance	C_{res}	—	16	—	pF	$f = 1\text{ MHz}$
Switching time	$t_{d(on)}$	—	48	—	ns	$I_C = 30\text{ A}, \text{Resistive Load}$ $V_{CC} = 300\text{ V}$ $V_{GE} = 15\text{ V}$ $R_g = 5\ \Omega$
	t_r	—	68	—	ns	
	$t_{d(off)}$	—	95	—	ns	
	t_f	—	55	—	ns	

Notes: 6. Pulse test

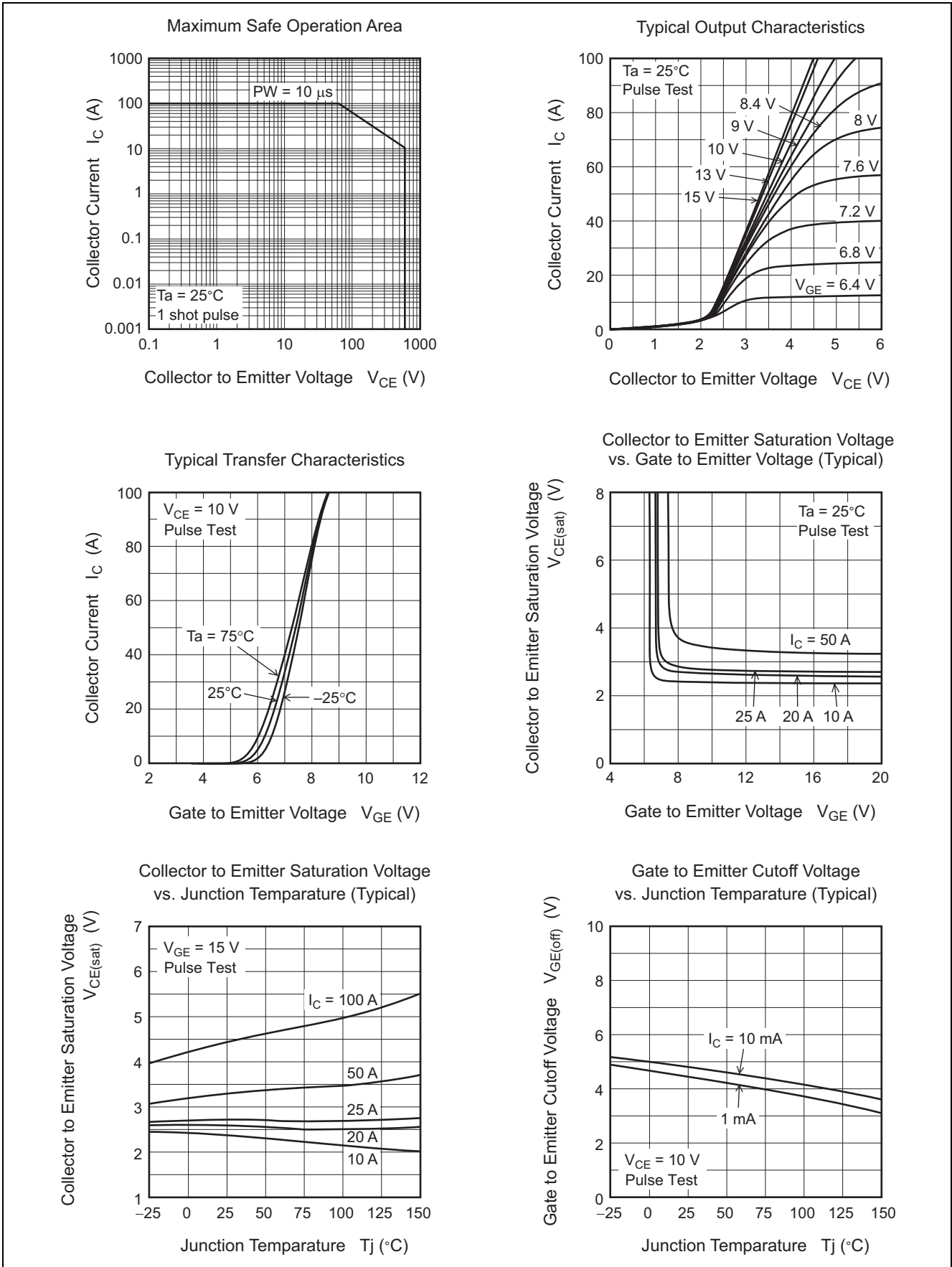
Diode

(Tj = 25°C)

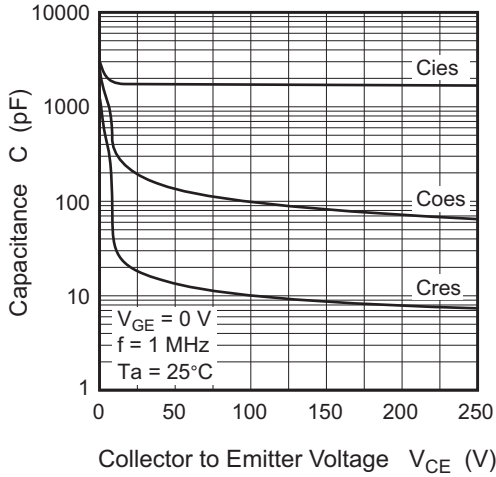
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Forward voltage	V_F	—	1.2	1.8	V	$I_F = 20\text{ A}$
Reverse current	I_R	—	—	10	μA	$V_R = 600\text{ V}$
Reverse recovery time	t_{rr}	—	100	—	ns	$I_F = 20\text{ A}$ $di/dt = -100\text{ A}/\mu\text{s}$
FRD reverse recovery charge	Q_{rr}	—	0.29	—	μC	
FRD peak reverse recovery current	I_{rr}	—	5.9	—	A	

Main Characteristics

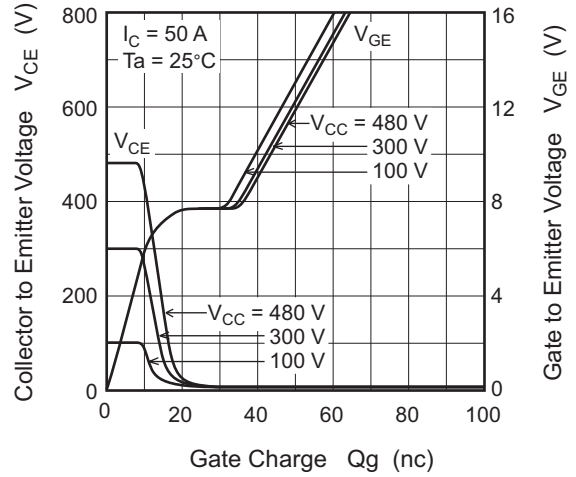
IGBT



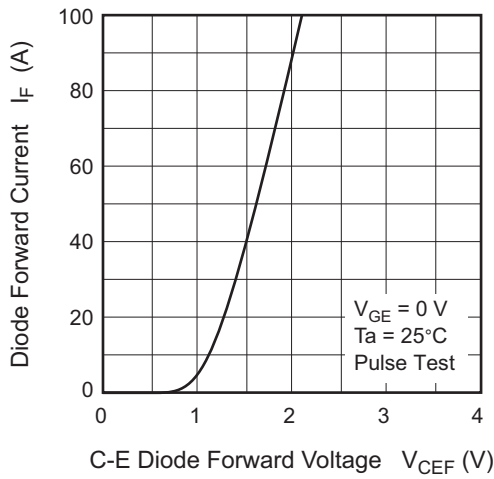
Typical Capacitance vs. Collector to Emitter Voltage



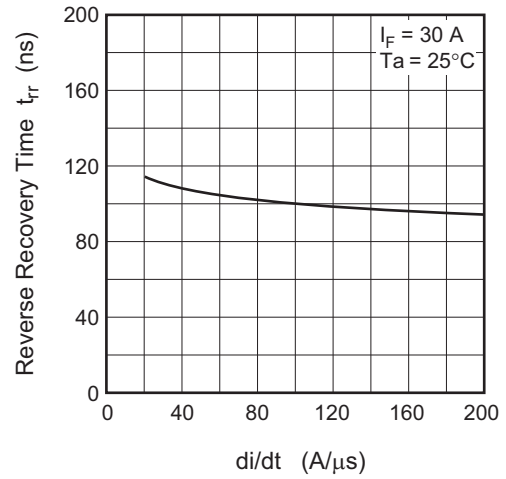
Dynamic Input Characteristics (Typical)



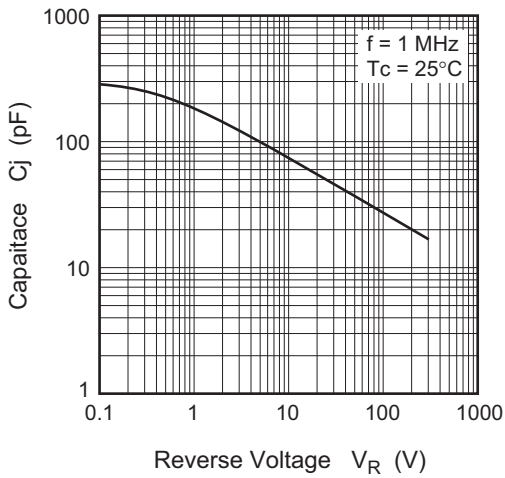
Forward Current vs. Forward Voltage (Typical)



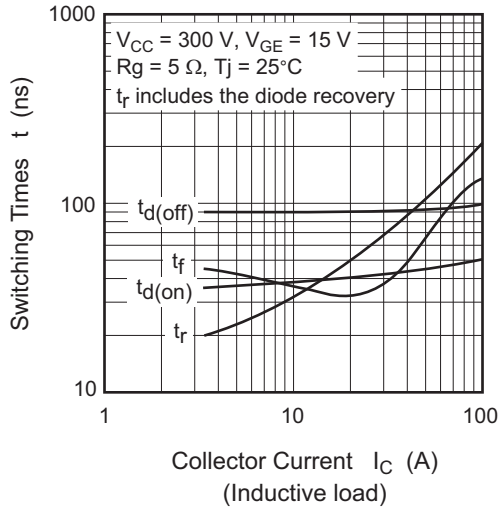
Reverse Recovery Time vs. di/dt (Typical)



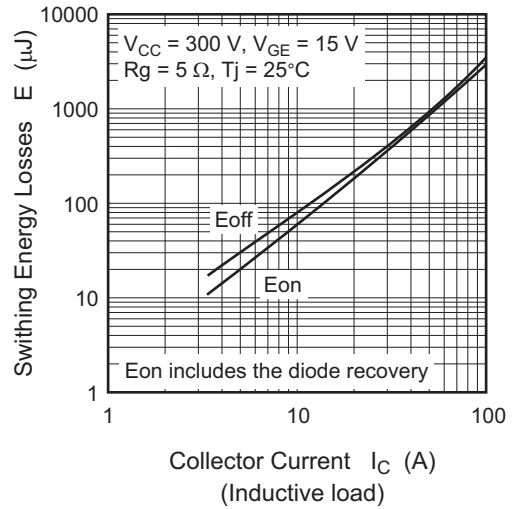
Capacitance vs. Reverse Voltage (Typical)



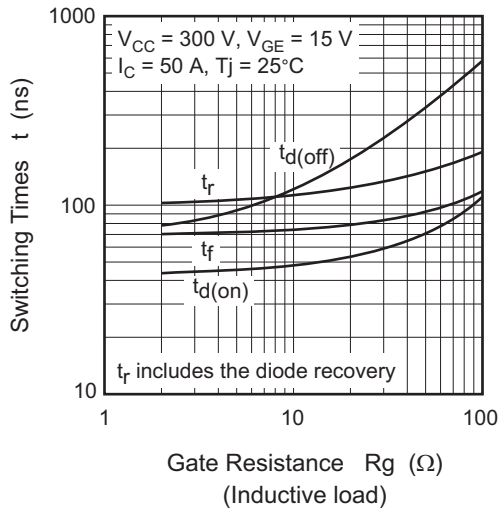
Switching Characteristics (Typical) (1)



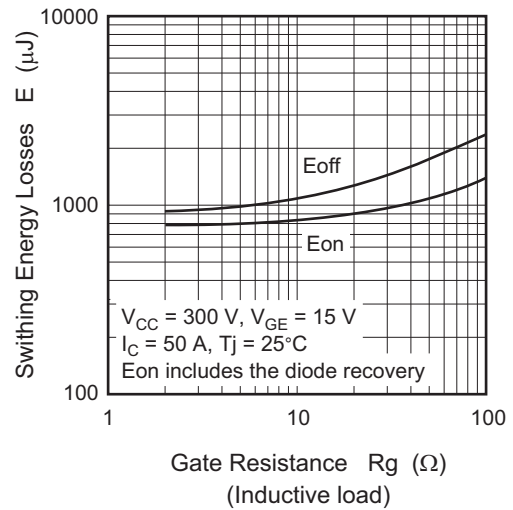
Switching Characteristics (Typical) (2)



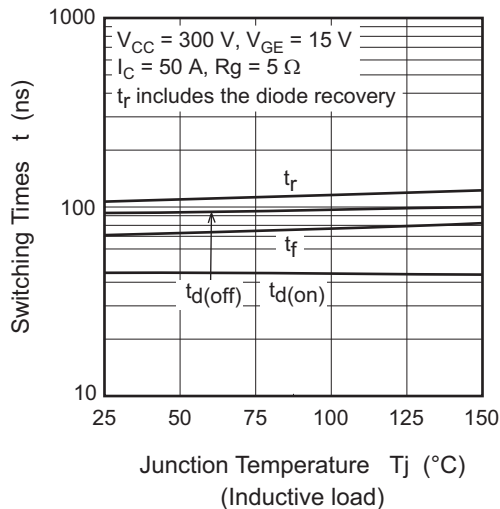
Switching Characteristics (Typical) (3)



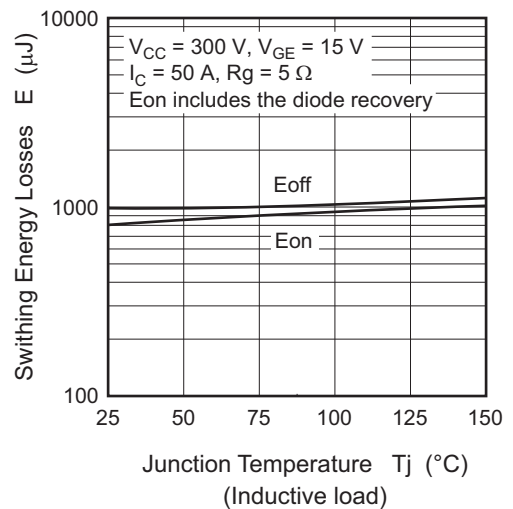
Switching Characteristics (Typical) (4)

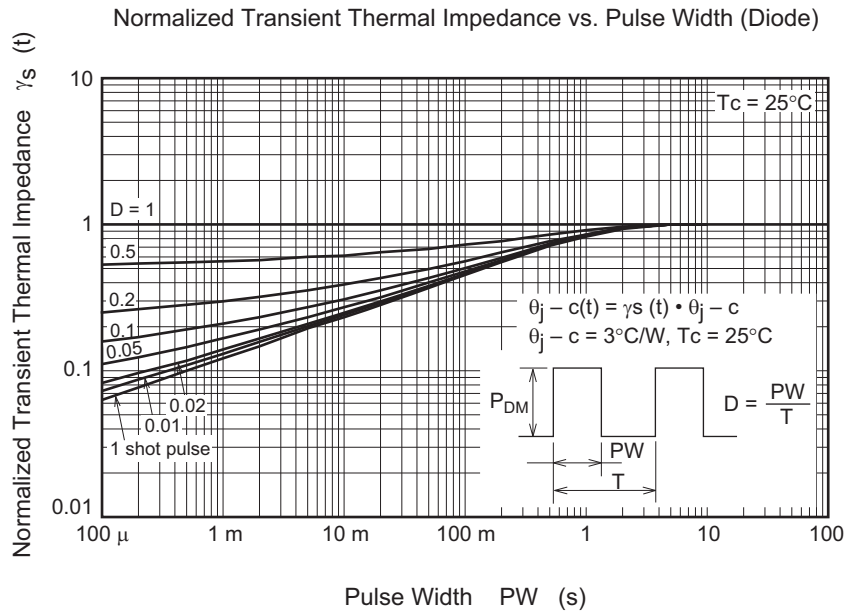
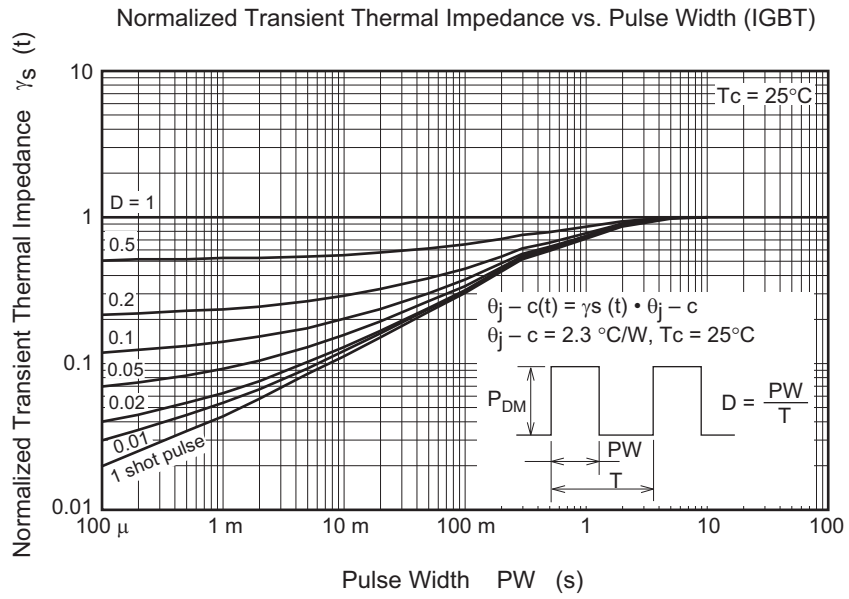


Switching Characteristics (Typical) (5)

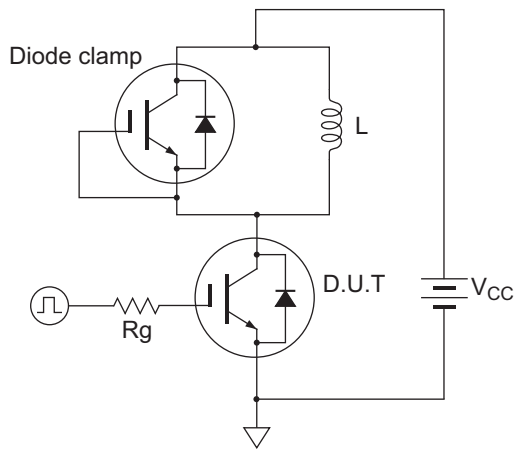


Switching Characteristics (Typical) (6)

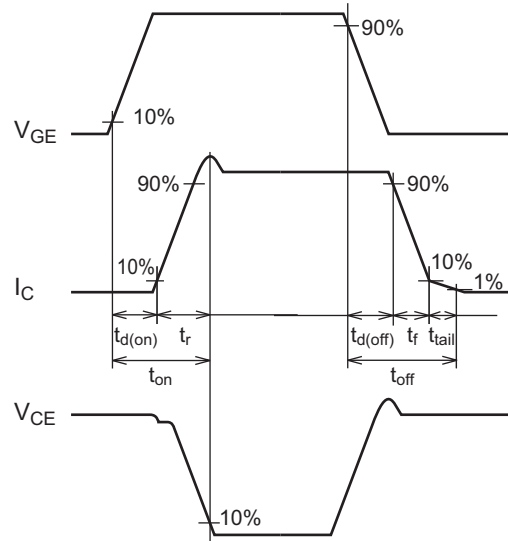




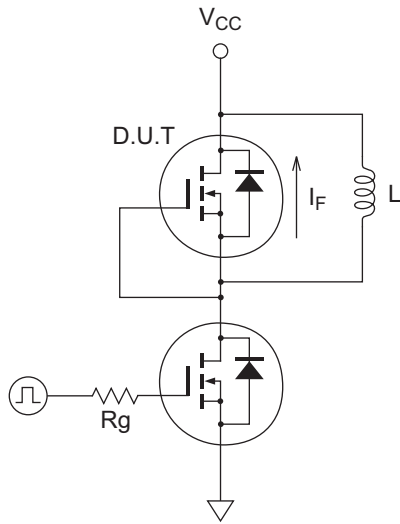
Switching Time Test Circuit



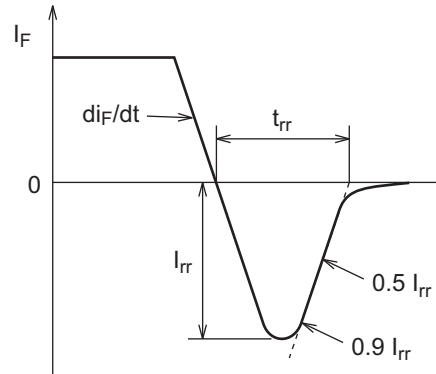
Waveform



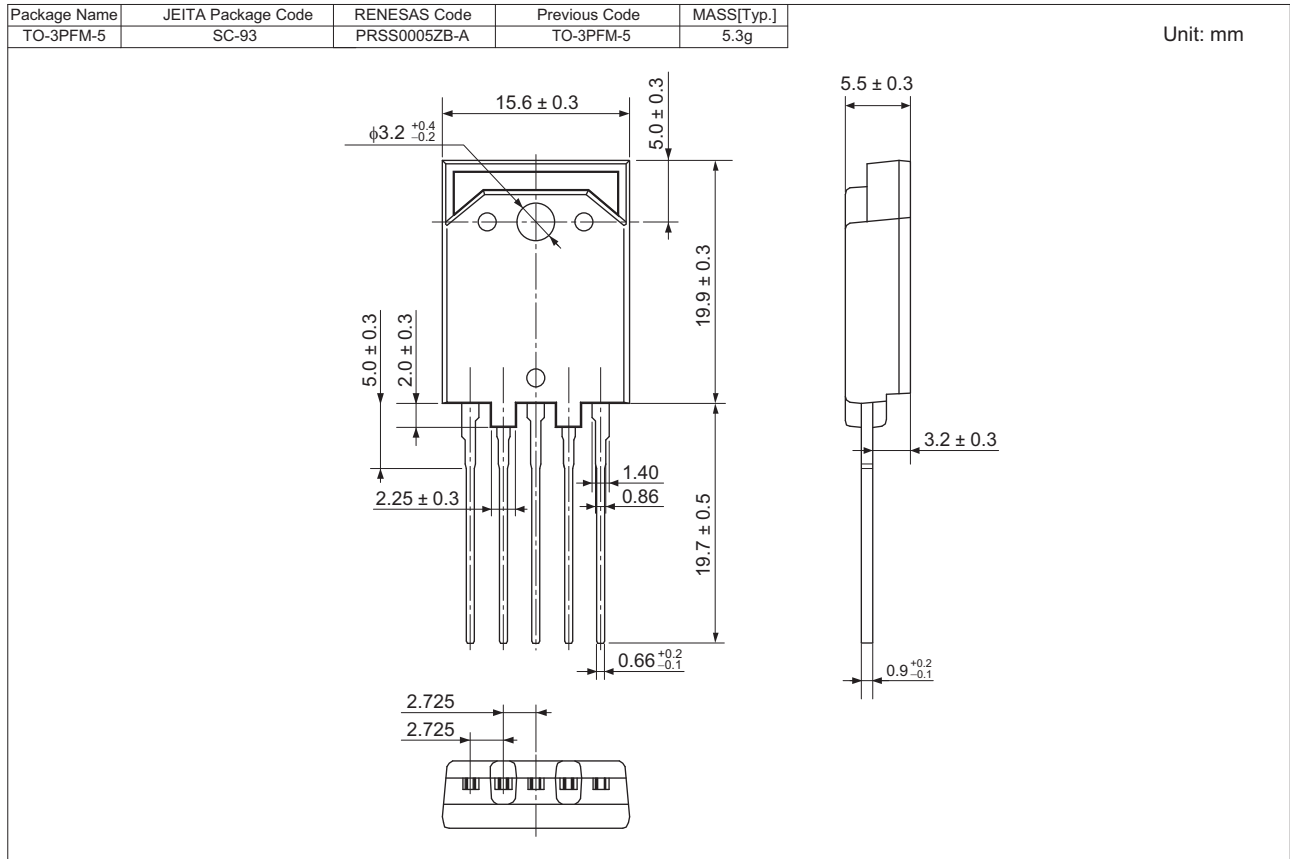
Diode Reverse Recovery Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJQ6008DPM-00#T0	360 pcs	Box (tube)

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